

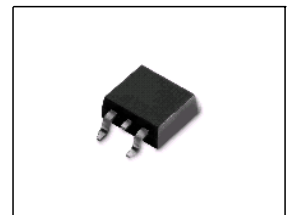
Fast Switching Emitter Controlled Diode Feature

- 1200 V Emitter Controlled technology
- Fast recovery
- Soft switching
- Low reverse recovery charge
- Low forward voltage
- Easy paralleling
- Qualified according to JEDEC⁰⁾ for target applications

Product Summary

V_{RRM}	1200	V
I_F	18	A
V_F	1.65	V
T_{jmax}	150	°C

PG-TO263-3-2



Type	Package	Ordering Code	Marking	Pin 1	PIN 2	PIN 3
IDB18E120	PG-TO263-3-2	-	D18E120	NC	C	A

Maximum Ratings, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Repetitive peak reverse voltage	V_{RRM}	1200	V
Continuous forward current	I_F	18	A
$T_C=25\text{ °C}$		31	
$T_C=90\text{ °C}$		19.8	
Surge non repetitive forward current	I_{FSM}	78	
$T_C=25\text{ °C}$, $t_p=10\text{ ms}$, sine halfwave			
Maximum repetitive forward current	I_{FRM}	47	
$T_C=25\text{ °C}$, t_p limited by T_{jmax} , $D=0.5$			
Power dissipation	P_{tot}	113	W
$T_C=25\text{ °C}$		113	
$T_C=90\text{ °C}$		54	
Operating and storage temperature	T_j, T_{stg}	-55...+150	°C
Soldering temperature reflow soldering, MSL1	T_S	260	°C

